

PEMH20; PUMH20

NPN/NPN resistor-equipped transistors;

R1 = 2.2 k Ω , R2 = 2.2 k Ω

Rev. 04 — 15 November 2009

Product data sheet

1. Product profile

1.1 General description

NPN/NPN resistor-equipped transistors.

Table 1. Product overview

Type number	Package		NPN/PNP complement	PNP/PNP complement
	NXP	JEITA		
PEMH20	SOT666	-	PEMD20	PEMB20
PUMH20	SOT363	SC-88	PUMD20	PUMB20

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

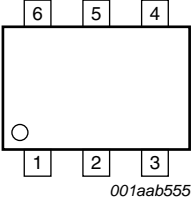
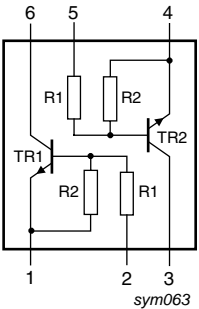
1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	k Ω
R2/R1	bias resistor ratio		0.8	1	1.2	

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1		

3. Ordering information

Table 4. Ordering information

Type number	Package		Version
	Name	Description	
PEMH20	-	plastic surface mounted package; 6 leads	SOT666
PUMH20	SC-88	plastic surface mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMH20	6K
PUMH20	H7*

[1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
Per transistor						
V_{CB0}	collector-base voltage	open emitter	-	50	V	
V_{CEO}	collector-emitter voltage	open base	-	50	V	
V_{EBO}	emitter-base voltage	open collector	-	10	V	
V_I	input voltage					
	positive		-	+12	V	
	negative		-	-10	V	
I_O	output current (DC)		-	100	mA	
I_{CM}	peak collector current		-	100	mA	
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$				
	SOT363		[1]	-	200	mW
	SOT666		[1][2]	-	200	mW
T_{stg}	storage temperature		-65	+150	$^\circ\text{C}$	
T_j	junction temperature		-	150	$^\circ\text{C}$	
T_{amb}	ambient temperature		-65	+150	$^\circ\text{C}$	
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$				
	SOT363		[1]	-	300	mW
	SOT666		[1][2]	-	300	mW

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	625	K/W
	SOT666		[1][2]	-	625	K/W
Per device						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	416	K/W
	SOT666		[1][2]	-	416	K/W

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

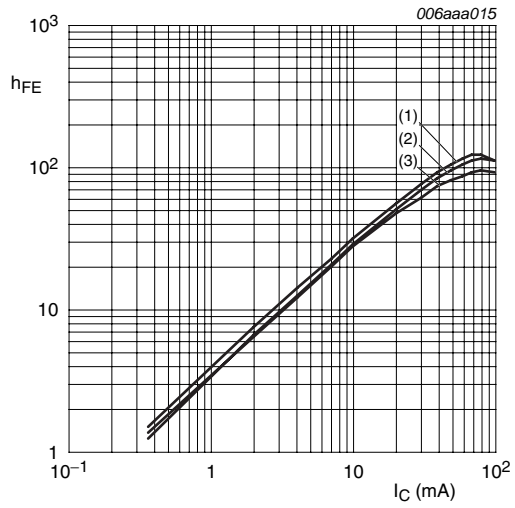
[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8. Characteristics

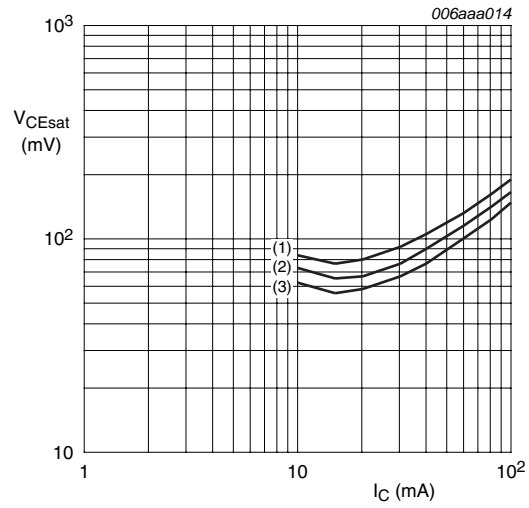
T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0 A	-	-	1	μ A
		V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C	-	-	50	μ A
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A	-	-	2	mA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 20 mA	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA	-	-	150	mV
V _{I(off)}	off-state input voltage	V _{CE} = 5 V; I _C = 1 mA	-	1.2	0.5	V
V _{I(on)}	on-state input voltage	V _{CE} = 0.3 V; I _C = 20 mA	2	1.6	-	V
R1	bias resistor1 (input)		1.54	2.2	2.86	k Ω
R2/R1	bias resistor ratio		0.8	1	1.2	
C _c	collector capacitance	V _{CB} = 10 V; I _E = i _e = 0 A; f = 1 MHz	-	-	2.5	pF



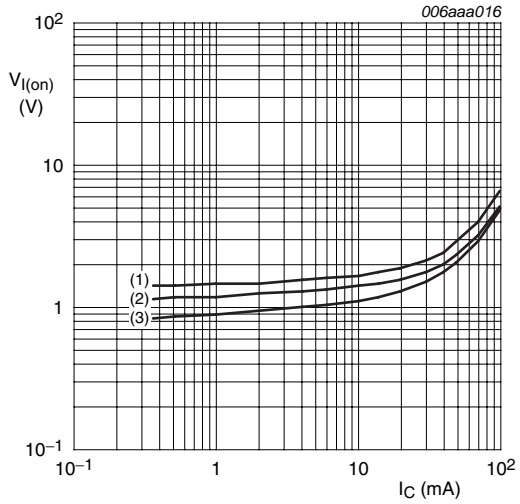
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 150\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -40\text{ }^\circ\text{C}$

Fig. 1. DC current gain as a function of collector current; typical values



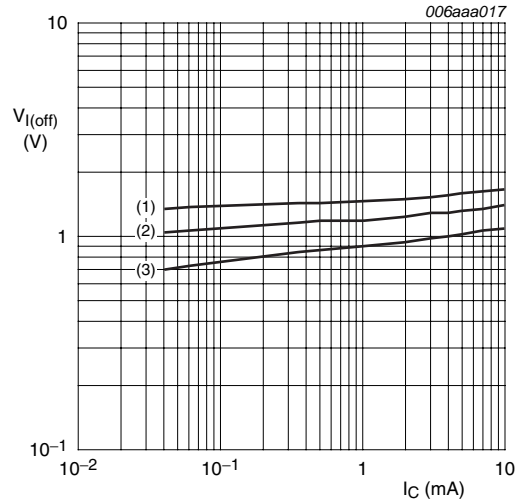
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -40\text{ }^\circ\text{C}$

Fig. 2. Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CE} = 0.3\text{ V}$
 (1) $T_{amb} = -40\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

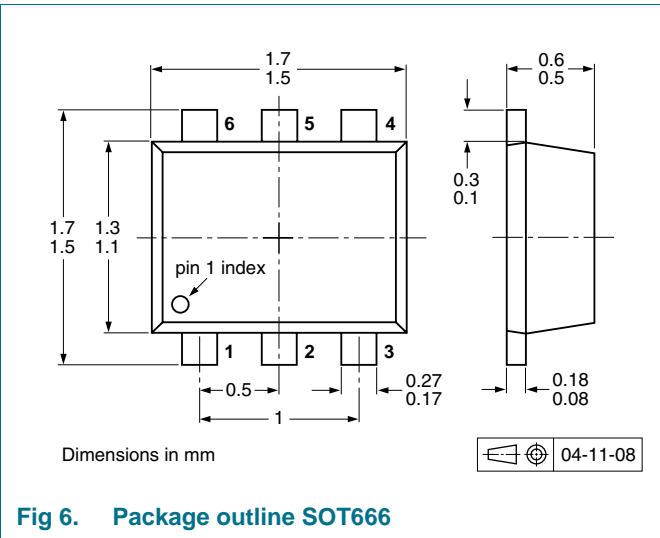
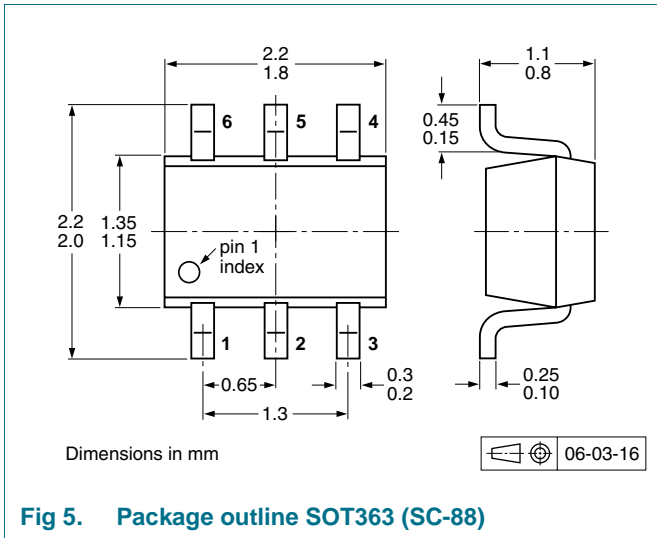
Fig. 3. On-state input voltage as a function of collector current; typical values



$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -40\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

Fig. 4. Off-state input voltage as a function of collector current; typical values

8. Package outline



9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity			
			3000	4000	8000	10000
PEMH20	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMH20	SOT363	4 mm pitch, 8 mm tape and reel; T1 ^[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2 ^[3]	-125	-	-	-165

[1] For further information and the availability of packing methods, see [Section 12](#).

[2] T1: normal taping

[3] T2: reverse taping

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMH20_PUMH20_4	20091115	Product data sheet	-	PEMH20_PUMH20_3
Modifications:	<ul style="list-style-type: none"> This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. Figure 5 "Package outline SOT363 (SC-88)"; updated 			
PEMH20_PUMH20_3	20050214	Product data sheet	-	PUMH20_2
PUMH20_2	20040414	Product specification	-	PUMH20_1
PUMH20_1	20031016	Product specification	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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13. Contents

1 Product profile 1

1.1 General description 1

1.2 Features 1

1.3 Applications 1

1.4 Quick reference data 1

2 Pinning information 2

3 Ordering information 2

4 Marking 2

5 Limiting values 3

6 Thermal characteristics 4

7 Characteristics 4

8 Package outline 6

9 Packing information 6

10 Revision history 7

11 Legal information 8

11.1 Data sheet status 8

11.2 Definitions 8

11.3 Disclaimers 8

11.4 Trademarks 8

12 Contact information 8

13 Contents 9

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